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ABSTRACT

A structure and method for connecting two levels of interconnect (22a, 22b) vertically spaced from each other by another level of interconnect by forming a first interconnect region (27) to which contact is to be made, a first insulating layer (24) over the interconnect region (27), and an etch-stop layer (26) over the first insulating layer (24), and etching the etch stop layer (26) to form an opening at a position over the first interconnect region (27). A second interconnect region (29) is in contact with the first insulating layer (24) and above the first interconnect region (27), a second insulating layer (28) is over the first insulation layer (24) and the etch stop layer (26), and an opening is formed in the second insulating layer (28) overlapping the opening in the etch stop layer (26). The opening in the second insulating layer (28) extended through the first insulating layer (24) creating a connection between the first interconnect region (27) and a region above the second insulating layer (28).

Fig. 2